

## Dual N-Channel 100-V (D-S) MOSFET

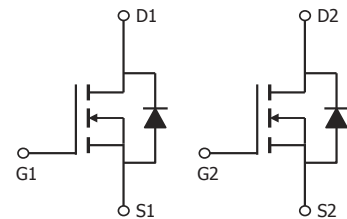
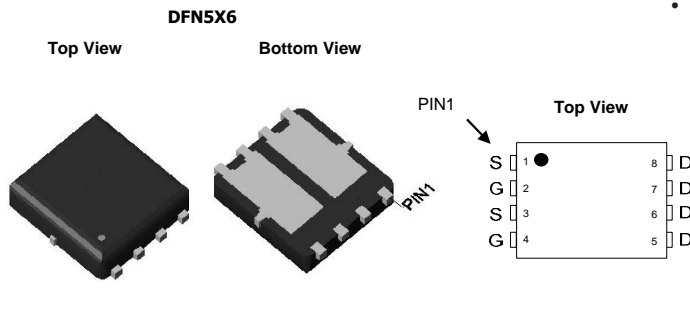
PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>d</sup>	Q <sub>g</sub> (Typ.)
100	0.148 at V <sub>GS</sub> = 10 V	15	15 nC
	0.155 at V <sub>GS</sub> = 4.5 V	10	

### FEATURES

- TrenchFET II Power MOSFET
- 100 % R<sub>g</sub> and UIS Tested

### APPLICATIONS

- Notebook System Power
- Synchronous Buck Converter
- Notebook Vcore



N-Channel MOSFET    N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	100	V	
Gate-Source Voltage	V <sub>GS</sub>	± 20		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	15 <sup>a</sup>	A
		T <sub>C</sub> = 70 °C	12	
		T <sub>A</sub> = 25 °C	g <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	6 <sup>b, c</sup>	
Pulsed Drain Current	I <sub>DM</sub>	45	mJ	
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C		15
		T <sub>A</sub> = 25 °C		g <sup>b, c</sup>
Avalanche Current	I <sub>AS</sub>	15		mJ
Single-Pulse Avalanche Energy	E <sub>AS</sub>	26		
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	21	W
		T <sub>C</sub> = 70 °C	16	
		T <sub>A</sub> = 25 °C	g <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	6 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>b, d</sup>	R <sub>thJA</sub>	55	65	°C/W	
Maximum Junction-to-Foot (Drain)	R <sub>thJF</sub>	16	20		

- Notes:
- Package limited.
  - Surface mounted on 1" x 1" FR4 board.
  - t = 10 s.
  - Maximum under Steady State conditions is 85 °C/W.

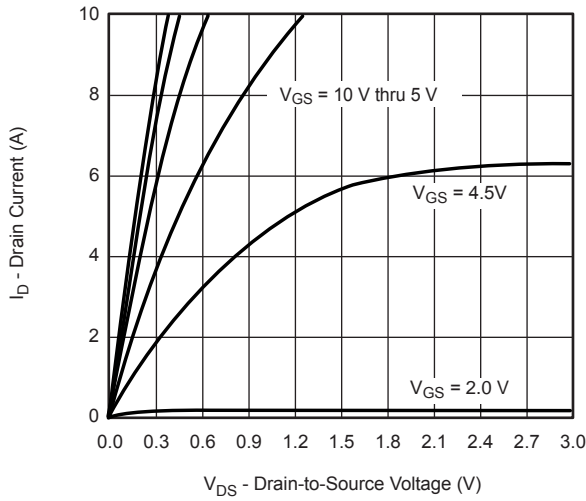
<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	100			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		55		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			-6.3		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1		4	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	15			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 5\text{ A}$		0.148	0.178	$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$		0.155	0.190	$\Omega$
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 10\text{ V}, I_D = 5\text{ A}$		40		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		2350		pF
Output Capacitance	$C_{oss}$			930		
Reverse Transfer Capacitance	$C_{rss}$			510		
Total Gate Charge	$Q_g$	$V_{DS} = 80\text{ V}, V_{GS} = 10\text{ V}, I_D = 5\text{ A}$		35		nC
Gate-Source Charge	$Q_{gs}$			6.3		
Gate-Drain Charge	$Q_{gd}$			11		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$		4.9	6.2	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 80\text{ V}, R_L = 3\text{ }\Omega$ $I_D \approx 5\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		16	19	ns
Rise Time	$t_r$			35	66	
Turn-Off Delay Time	$t_{d(off)}$			30	39	
Fall Time	$t_f$			26	31	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 80\text{ V}, R_L = 3\text{ }\Omega$ $I_D \approx 5\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		9	18	
Rise Time	$t_r$			15	15	
Turn-Off Delay Time	$t_{d(off)}$			19	28	
Fall Time	$t_f$			20	35	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			15	A
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				45	
Body Diode Voltage	$V_{SD}$	$I_S = 2\text{ A}$		0.7	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 4.5\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		26	55	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			26	55	nC
Reverse Recovery Fall Time	$t_a$			20		ns
Reverse Recovery Rise Time	$t_b$			7		

Notes:

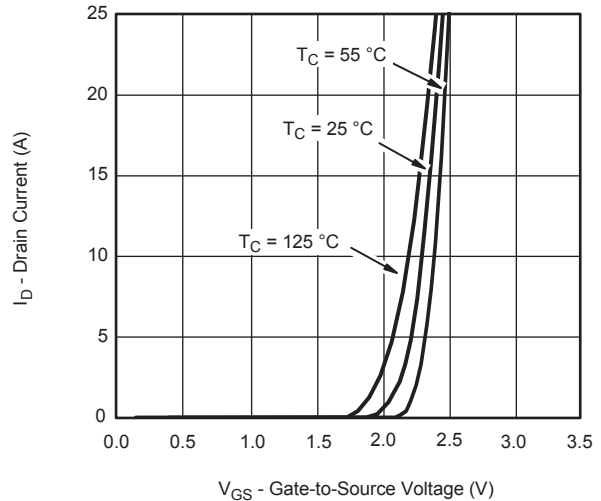
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

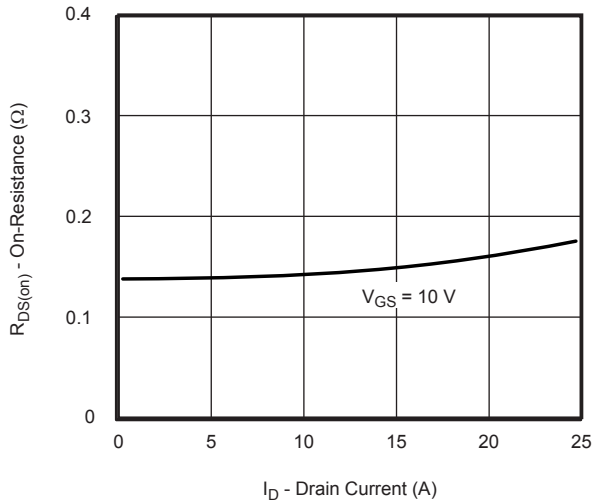
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



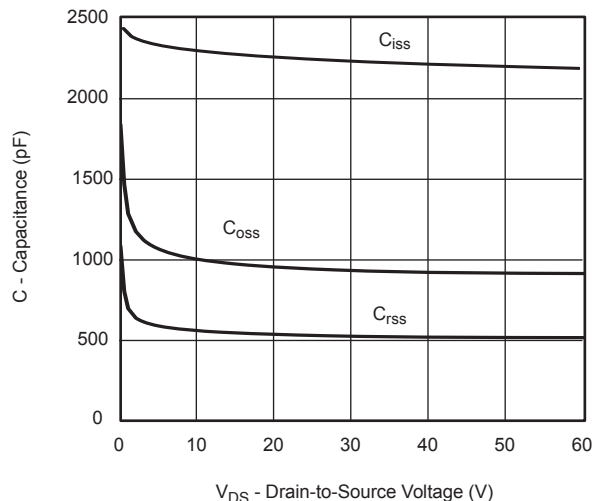
**Output Characteristics**



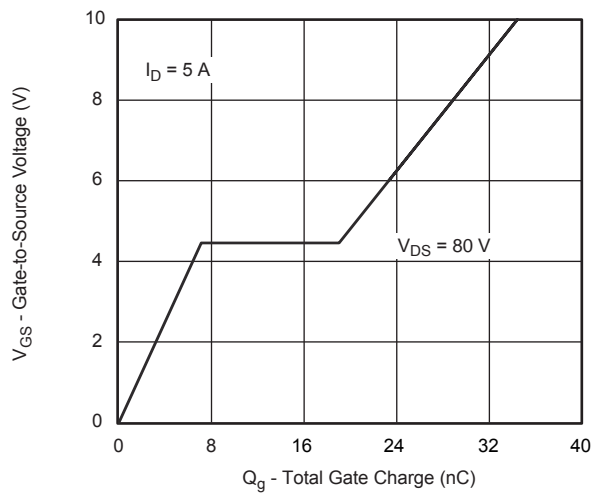
**Transfer Characteristics**



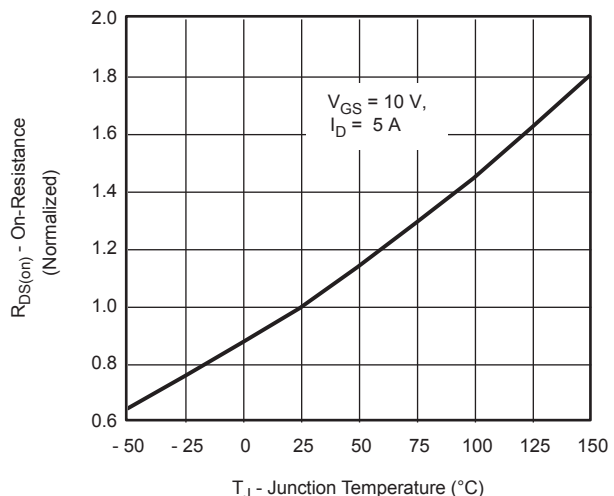
**On-Resistance vs. Drain Current**



**Capacitance**

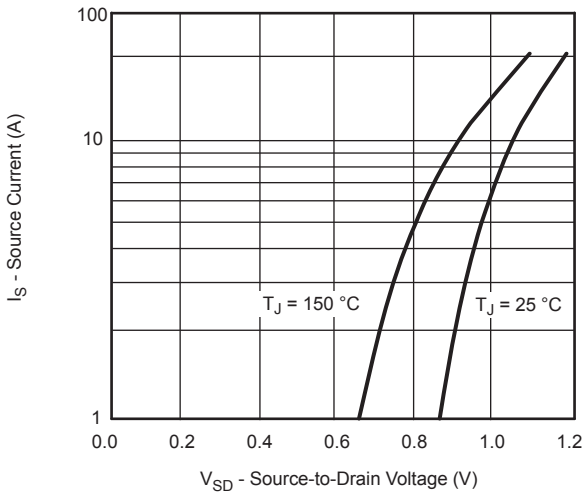


**Gate Charge**

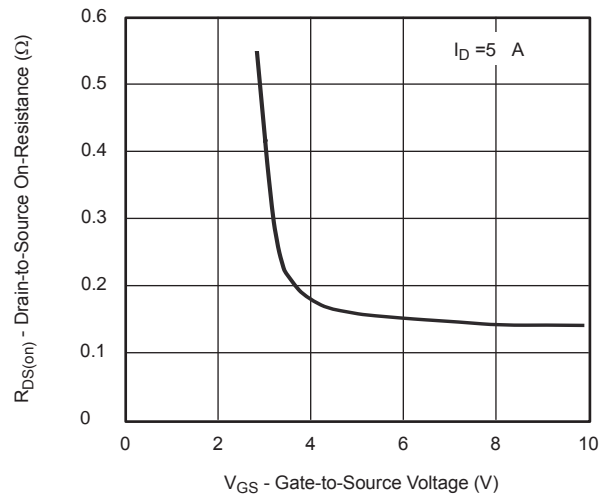


**On-Resistance vs. Junction Temperature**

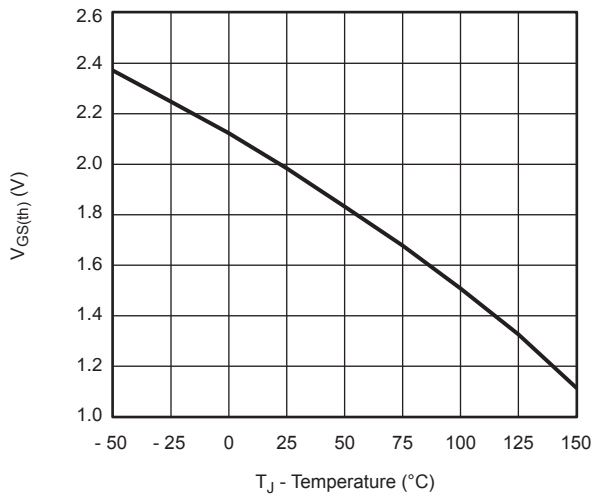
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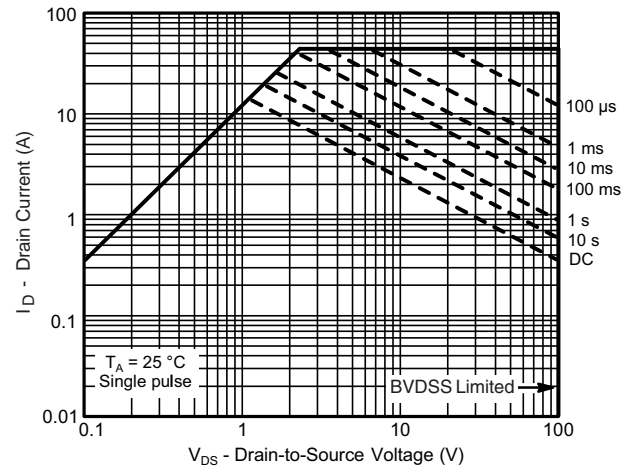
**Source-Drain Diode Forward Voltage**



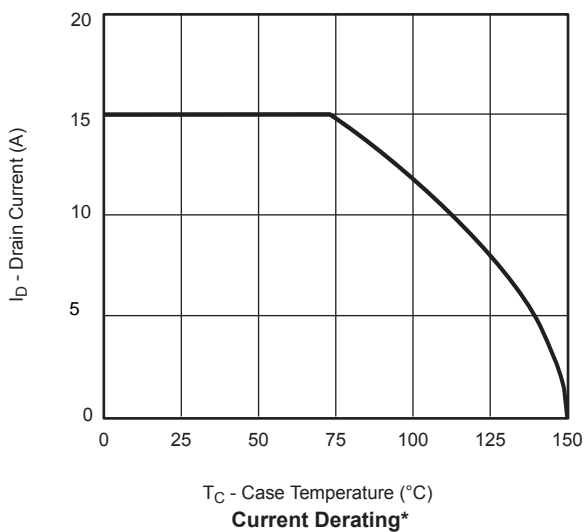
**On-Resistance vs. Gate-to-Source Voltage**



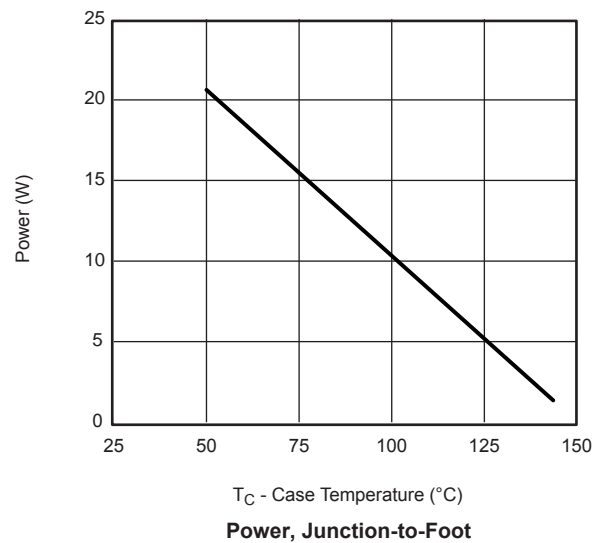
**Threshold Voltage**



**Safe Operating Area, Junction-to-Ambient**

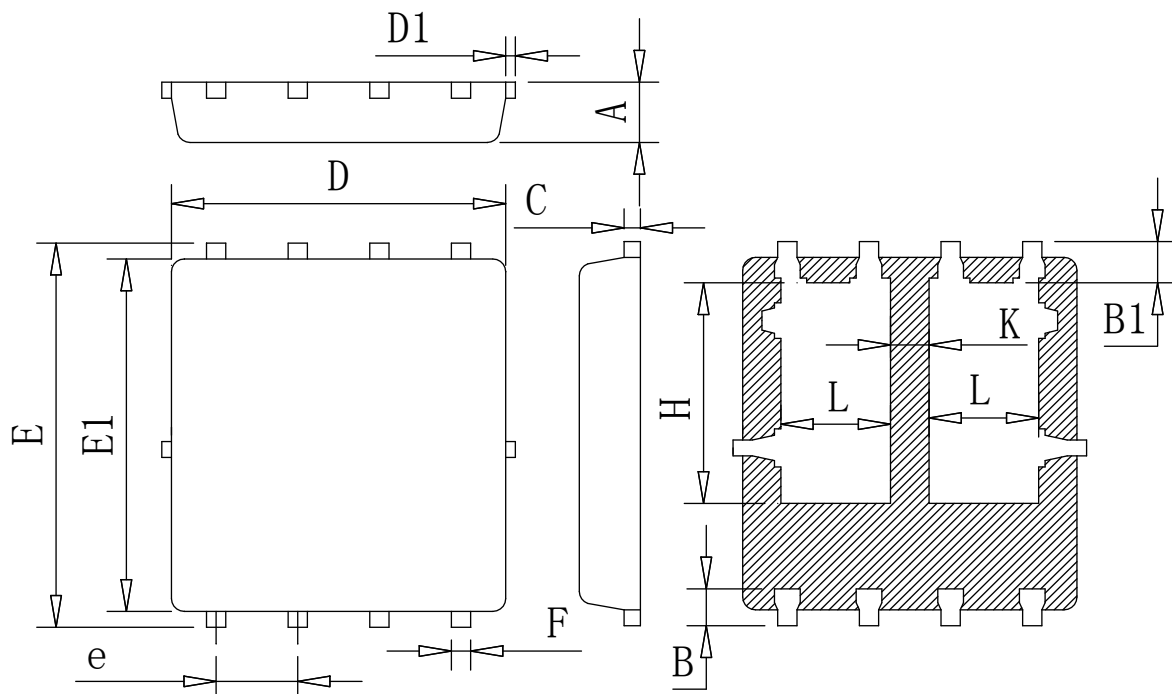


**Current Derating\***



**Power, Junction-to-Foot**

## DFN5X6-8L-D PACKAGE OUTLINE



COMMON DIMENSIONS  
(UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Typ	Max
A	0.85	0.95	1.05
B	0.46	0.58	0.73
B1	0.52	0.65	0.78
C	0.18	0.254	0.32
D	4.70	5.20	5.50
D1	-	-	0.18
E	5.75	6.05	6.35
E1	5.35	5.65	5.85
e	1.15	1.27	1.50
F	0.15	0.30	0.50
H	3.15	3.47	3.80
L	1.35	1.70	2.10
K	0.35	0.60	1.00

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